

### LM96550 Ultrasound Transmit Pulser

Check for Samples: LM96550

### **FEATURES**

- 8-Channel High-Voltage CMOS Pulse Generator
- Output Pulses with ±50V and 2A Peak Current
- Active Damper with Built-In Blocking Diodes
- Up to 15 MHz Operating Frequency
- Matched Delays for Rising and Falling Edges
- Low Second Harmonic Distortion Allows and Improves Harmonic Imaging
- Continuous-Wave (CW) Operation Down to ±3.3V
- Low Phase Noise Enables Doppler **Measurements** 
  - 145 dBc/Hz Phase Noise at 10 MHz (1 kHz offset)
- **Output State Over-Temperature Protection** •
- **Blocking Diodes for Direct Interface to** Transducer
- 2.5V to 5.0V CMOS Logic Interface
- Low-Power Consumption per Channel
- **Over Temperature Protection**

### **KEY SPECIFICATIONS**

- Output Voltage: ±50 V
- Output Peak Current: ±2.0 A
- Output Pulse Rate: Up to 15 MHz
- Rise/fall Delay Matching (Max): < 3 ns
- Pulser HD2 (5 MHz): -40 dB
- Operating Temp. : 0 to +70 °C

### APPLICATIONS

Ultrasound Imaging

### DESCRIPTION

The LM96550 is an eight-channel monolithic highvoltage, high-speed pulse generator for multi-channel medical ultrasound applications. It is well-suited for use with TI's LM965XX series chipset which offers a complete medical ultrasound solution targeted towards low-power, portable systems.

The LM96550 contains eight high-voltage pulsers with integrated diodes generating ±50V bipolar pulses with peak currents of up to 2A and pulse rates of up to 15 MHz. Advanced features include low-jitter and low-phase-noise output pulses ideal for continuouswave (CW) modes of operation. Active clamp circuitry is integrated for ensuring low harmonic distortion of the output signal waveform.

The LM96550 also features a low-power operation mode and over-temperature protection (OTP) which are enabled by on-chip temperature sensing and power-down logic.

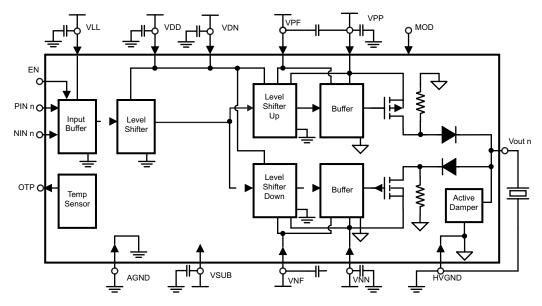


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#### **BLOCK DIAGRAM**



#### **Typical Application**

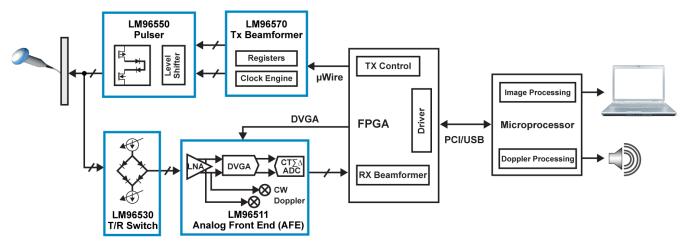


Figure 1. 8-Channel Transmit/Receive Chipset



**Pin Diagram** 

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#### HVGND HVGND HVGND HVGND HVGND HVGND HVGND HVGND Vout3 Vout6 Vout1 Vout1 Vout2 Vout2 Vout3 Vout4 Vout4 Vout5 Vout5 Vout6 80 79 77 70 69 62 61 78 76 75 74 72 71 68 67 66 64 63 65 73 Vout0 1 60 Vout7 Vout0 2 59 Vout7 58 HVGND 3 0: VSUB HVGND VPP 4 57 VPP VPP 5 56 VPP VPP 55 VPP 6 VPF 54 VPP 7 VPF 53 VPF 8 52 HVGND 9 HVGND VNF 10 51 VNF LM96550 VNN 11 50 VNN VNN 49 VNN 12 VNN 13 48 VNN 47 VNN VNN 14 VSUB 46 VSUB 15 45 VDN VDN 16 44 AGND AGND 17 VDD 18 43 VDD 42 AGND 19 AGND 41 VLL 20 VLL 40 22 24 25 26 29 30 31 32 33 34 35 36 37 38 39 21 23 27 28 MODE Pin0 Nin0 Pin2 Nin2 Nin3 Ц OTP AGND Pin4 Pin5 Nin5 Pin6 Nin6 Pin7 Nin7 Pin3 Nin4 Nin1 Pin1 Figure 2. WQFN Pin Diagram of LM96550

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		PIN DE	SCRIPTIONS			
Pin No.	Name	Туре	Function and Connection			
21, 23, 25, 27, 33, 35, 37, 39	PIN n=07	Input	Logic control positive output channel P 1 = ON 0 = OFF			
22, 24, 26, 28, 34, 36, 38, 40	NIN n=07	Input	Logic control negative output channel N 1 = ON 0 = OFF			
59, 60	V <sub>OUT7</sub>					
62, 63	V <sub>OUT6</sub>					
65, 66	V <sub>OUT5</sub>					
68, 69	V <sub>OUT4</sub>	Output				
72, 73	V <sub>OUT3</sub>	Output	High voltage output of channels 0 to 7			
75, 76	V <sub>OUT2</sub>	_				
78, 79	V <sub>OUT1</sub>					
1, 2	V <sub>OUT0</sub>					
29	EN	Input	Chip power enable 1 = ON 0 = OFF			
31	MODE	Input	Output current mode control 1 = Max Current 0 = Low Current			
30	OTP	Output	Over-temperature indicating IC temp > 125°C 0 = Over-temperature 1 = Normal temperature This pin is open-drain.			
4, 5, 6, 7, 54, 55, 56, 57	VPP	Power	Positive high voltage power supply (+3.3V to +50V)			
11, 12, 13, 14, 47, 48, 49, 50	VNN	Power	Negative high voltage power supply (-3.3V to -50V)			
8, 53	VPF	Power	Positive floating power supply (VPP -10V)			
10, 51	VNF	Power	Negative floating power supply (VNN +10V)			
18, 43	VDD	Power	Positive level-shifter supply voltage (+10V)			
16, 45	VDN	Power	Negative level-shifter supply voltage (-10V)			
20, 41	VLL	Power	Logic supply voltage. Hi voltage reference input (+2.5 to +5V)			
0, 15, 46	VSUB	Power	All VSUB pins must be connected to most negative potential of the IC. NOTE: The exposed thermal pad is connected to VSUB.			
3, 9, 52, 58, 61, 64, 67, 70, 71, 74, 77, 80	HVGND	Ground	High voltage reference potential (0V)			
17, 19, 32, 42, 44	AGND	Ground	Analog and Logic voltage reference input, logic ground (0V)			

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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### ABSOLUTE MAXIMUM RATINGS (1)(2)

Maximum Junction Temperature (T <sub>JMAX</sub> )	+150°C
Storage Temperature Range	-40°C to +125°C
Supply Voltage (VDD)	-0.3V to +12V
Supply Voltage (VDN)	+0.3V and -12V
Supply Voltage (VPP)	–0.3V and +55V
Supply Voltage (VPF)	VPP -14V
Supply Voltage (VNN)	+0.3V and -55V
Supply Voltage (VNF)	VNN +14V
Supply Voltage (VSUB)	-65V
IO Supply Voltage (VLL)	-0.3V to +5.5V
Voltage at Logic Inputs	-0.3V to VLL +0.3V

(1) Absolute Maximum Ratings are limits beyond which damage to the device may occur. Operating Ratings are conditions under which operation of the device is ensured to be functional, but do not specify specific performance limits. For specifications and test conditions, see the Electrical Characteristics.

(2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.

### **OPERATING RATINGS**

Operation Junction Temperature		0°C to + 70°C
VPP, -VNN; High-voltage supply		+3.3V to +50V
VPF, -VNF; Floating supply	VPP -10V	
VDD, -VDN; Level-shift supply	+9V to 11V	
VLL, Logic Supply	+2.4V to +5.3V	
VSUB, Substrate bias supply	must be most negative supply	
Package Thermal Resistance (θ <sub>JA</sub> )		19.7°C/W
ESD Tolerance	Human Body Model	2kV
	Machine Model	150V
	Charge Device Model	750V

### ANALOG CHARACTERISTICS

Unless otherwise stated, the following conditions apply

VLL = +3.3V, VPP = -VNN = 50V, VPF = -VNF = VPP-10V, VDD = -VDN = 10V, VSUB = -55V, R<sub>L</sub> = 2 K $\Omega$ , T<sub>A</sub> = 25°C, Mode = LO, EN = HI, Fin=5MHz

Symbol	Parameter	Conditions	Min	Тур	Max	Units
F <sub>OUT</sub>	Output Frequency Range	$R_L = 100\Omega$	1		15	MHz
	Output Voltage Range		-48.5		+48.5	V
	Output Current	2% Duty Cycle		2		
	Output Current	100% Duty Cycle, Mode=HI		0.6		A
HD2	Second harmonic distortion	$R_{L} = 100\Omega    C_{L} = 330pF$ (See <sup>(1)</sup> )		-40		dBc
R <sub>ON</sub>	Output ON Resistance	100 mA		7	11	Ω
	Output clamp	Positive or Negative pulse		2		А

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#### **ANALOG CHARACTERISTICS (continued)**

Unless otherwise stated, the following conditions apply VLL = +3.3V, VPP = -VNN = 50V, VPF = -VNF = VPP-10V, VDD = -VDN = 10V, VSUB = -55V, R<sub>L</sub> = 2 K $\Omega$ , T<sub>A</sub> = 25°C, Mode = LO, EN = HI, Fin=5MHz

Symbol	Parameter	Conditions	5	Min	Тур	Max	Units
			VPP		0.7	3	- mA
	Power Supply Current		VNN		0.5	4.5	
			VDD		8	13	
			VDN		4	7	
		Pin = Nin = 0	VLL		25	50	μA
			VSUB		1.2	6	
			VPF		0.1	1.5	mA
			VNF		0.1	1.5	
			VPP		0.7	3	mA
		En = 0	VNN		0.5	4.5	
			VDD		0.4	2.7	
			VDN		0.1	2.2	
			VLL		25	50	μA
			VSUB		1.2	6	mA
			VPF		0.1	1.5	
			VNF		0.1	1.5	
)PT	Over Temperature Protection				125		°C
ОТР	OTP sigma				3.0		°C
Isys <sub>OTP</sub>	OTP hysteresis				5.5		°C

#### AC AND TIMING CHARACTERISTICS

Unless otherwise stated, the following conditions apply.

VLL = +3.3V, VDD = -VDN = 10V, VSUB = -55V, VPP = -VNN = 50V, VPF = -VNF = 40V, C<sub>L</sub> = 330pF, R<sub>L</sub> = 100  $\Omega$ , T<sub>A</sub> = 25°C, Fin=5MHz, Mode=LO, EN=HI

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>r</sub>	Output rise time	— See <sup>(1)</sup>		18	26	
t <sub>f</sub>	Output fall time			18 26	26	– ns
t <sub>E</sub>	Enable time			1		μs
t <sub>dr</sub>	Delay time on inputs rise	See <sup>(1)</sup>		32	39	
t <sub>df</sub>	Delay time on inputs fall			32	39	ns
t <sub>dr</sub> - t <sub>dr</sub>	Delay time mismatch	P-to-N See (1)(2)			3	
t <sub>dm</sub>	Delay on mode change			1		μs

(1) VNF = -42V, VPF = 38V

(2) The delay time mismatch can be adjust to be less than 0.8ns with the LM96570 duty cycle control function.

### **DC CHARACTERISTICS**

Unless otherwise stated, the following conditions apply.

VLL = +3.3V, VDD = -VDN = 10V, VSUB = -55V, VPP = -VNN = 50V, VPF = -VNF = 40V, T<sub>A</sub> =  $25^{\circ}C$ ,

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL</sub>	Low Input "LO" threshold				1	V
V <sub>IH</sub>	High Input "HI" threshold		2.3			V
I <sub>IN</sub>	input current			1		μA



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#### OVERVIEW

The LM96550 pulser provides an 8-channel transmit side solution for medical ultrasound applications suitable for integration into multi-channel (128/256 channel) systems. Its flexible, integrated ±50V pulser architecture enables low-power designs targeting portable systems. A complete system can be designed using TI's companion LM965XX chipset.

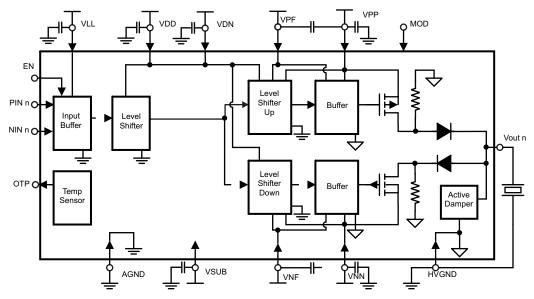


Figure 3. Block Diagram of High-Voltage Pulser Channel

A functional block diagram of the LM96550 is shown in Figure 3. It has an input buffer at its CMOS logic interface, which is powered by VLL (2.5 to 5.0V). When EN=HI, driving a channel's inputs (PIN n or NIN n) HI will result in a positive or negative pulse at the channel's output pin ( $V_{OUT}$  n), respectively. The output pins  $V_{OUT}$  are pulled to either the positive or negative supplies, VPP or VNN by power MOSFETs.

When PIN and NIN are both LO, Vout is actively clamped to GNDHI at 0V. This clamping reduces harmonic distortions compared to competing architectures that use bleeding resistors for implementing the return to zero of the output. The user must avoid the condition in which PIN and NIN are both HI simultaneously, as this will damage the output stage!

The impedance of the output stage can be controlled via the Mode-pin. When the Mode = HI as shown, only one output transistor pair drives the output resulting in a peak current of 600 mA at VPP = -VNN = 50V. When Mode=LO, a peak-current of 2A is achievable resulting in faster transients at the output. However, faster output transients can lead to significant overshoot of the output signal. This can be avoided using the lower drive current option.

Continuous-wave (CW) applications are supported for low power consumption down to VPP = -VNN = 3.3V with Mode =HI.

Internally, the CMOS logic input signals are level shifted to VDD = 10V and VDN = -10V for pulse transmission. The outputs of the level shifter drive the high-voltage P and N drivers that control the output power MOSFETs, which are supplied from the positive and negative rails VPP and VNN, respectively. The high-voltage rails are designed for a maximum of 50V; however, they can be operated down to 3.3V. The necessary gate-overdrive voltage levels for the output drivers are internally generated from the high-voltage rails.

Over-Temperature Protection (OTP) is implemented by continuously monitoring the on-chip temperature. The OTP output (open drain) pin goes LO when the chip temperature exceeds a critical level. Prior to this event, the user must ensure that the chip is powered down before fatal damage occurs. In addition to a primary software controlled safety shutdown, the OTP pin can be also be hard-wired to the EN pin as a secondary safety measure.

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### **Timing Diagrams**

### RISE AND FALL TIME

The timing diagram shown in Figure 4 defines the rise and fall times tr and tf.

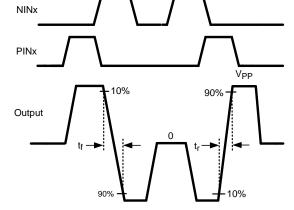


Figure 4. Timing Diagram Defining Rise and Fall Times tr and tf, respectively

### INPUT TO OUTPUT DELAY

The timing diagram shown in Figure 5 defines the delays between the input and output signals.

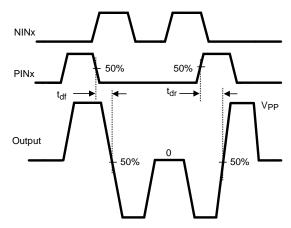


Figure 5. Timing Diagram Defining Input-to-Output Delays Times

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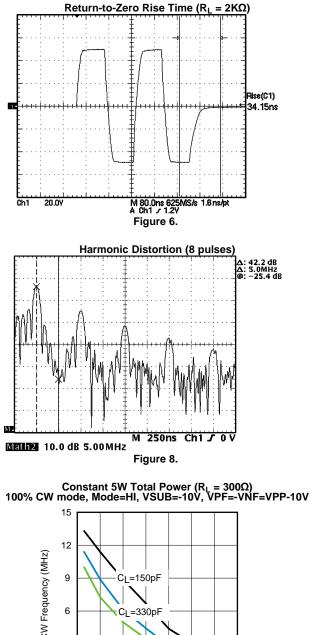


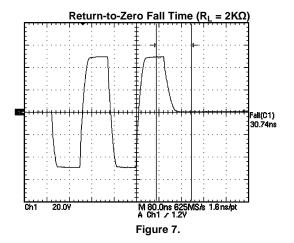
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#### **TYPICAL PERFORMANCE CHARACTERISTICS**

 $\label{eq:VLL} Unless otherwise stated, the following conditions apply. \\ VLL = +3.3V, VDD = -VDN = 10V, VSUB = -55V, VPP = -VNN = 50V, VPF = VPP-12V, VNF = VNN+8V, C_L = 330pF, R_L = 100\Omega, T_A = 25^{\circ}C, Fin=5MHz, Mode=LO, EN=HI$ 





Differential Input vs. Pulser Output Phase Noise<sup>(1)</sup>

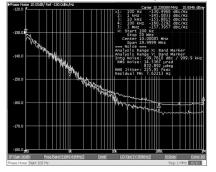
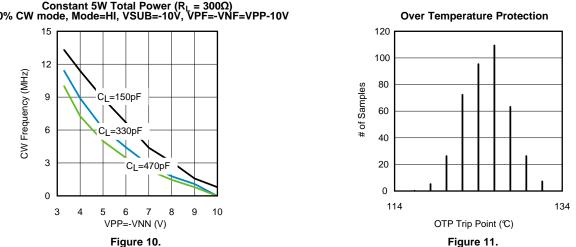


Figure 9.



 10.24 MHz Differential Input signal from LMK04800 Evaluation board with 122.88 MHz Crystek CVHD-950 VCXO clock source. The LMK04800 clock output channel was configured with a divide value of 12 and LVCMOS outputs with opposite polarity.

#### TEXAS INSTRUMENTS

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#### FUNCTIONAL DESCRIPTION

Note that the case, PINn = NNn = HI is not allowed as it will damage the output transistors.

	Logic inputs		Output
EN	PINn	NINn	Voutn
1	0	0	0V
1	1	0	VPP - 0.7V
1	0	1	VNN + 0.7V
1	1	1	not allowed
0	Х	Х	0V

#### **APPLICATIONS INFORMATION**

#### POWER-UP AND POWER-DOWN SEQUENCES

VSUB must always be the most negative supply, i.e., it must be equal to or more negative than the most negative supply, VNN or VDN. VPF  $\ge$  VPP -14V AND VNF =  $\le$  VNN +14V at all times.

Power UP Sequence:

- 1. Turn ON VSUB, hold EN pin LO
- 2. Turn ON VLL
- 3. Turn ON VDD, VDN, VPP, VPF, VNN and VNF

Power DOWN Sequence:

- 1. Turn OFF VDD, VDN, VPP, VPF, VNN and VNF
- 2. Turn OFF VLL
- 3. Turn OFF VSUB



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#### **REVISION HISTORY**

Cł	nanges from Revision E (May 2013) to Revision F P	age
•	Changed layout of National Data Sheet to TI format	. 10



1-Dec-2016

### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
LM96550SQX/NOPB	NRND	WQFN	NKF	80	2000	Green (RoHS & no Sb/Br)	CU SN   Call TI	Level-3-260C-168 HR		LM96550SQ	

<sup>(1)</sup> The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(<sup>6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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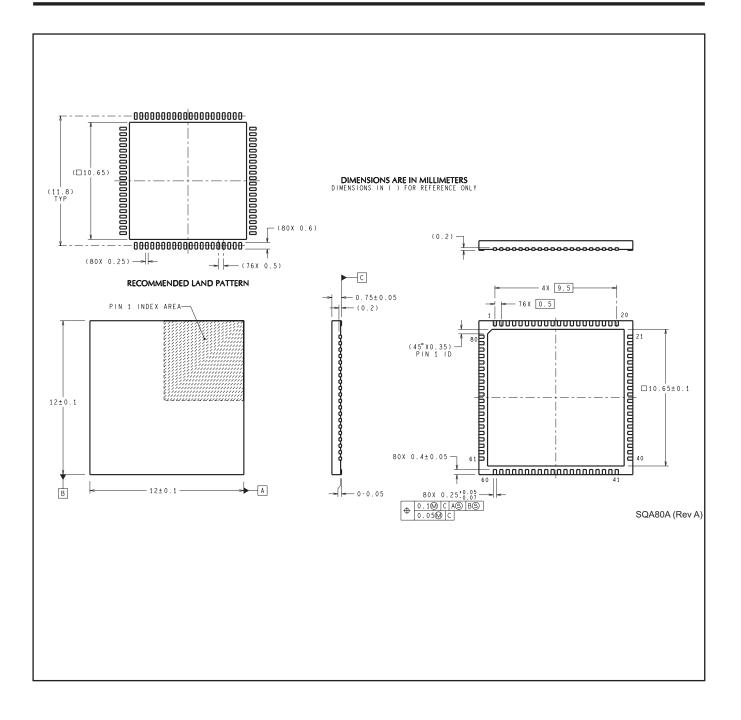


### PACKAGE OPTION ADDENDUM

1-Dec-2016

### **MECHANICAL DATA**

## NKF0080A





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